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PTO/SB/05 (4/98)
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UTILITY PATENT APPLICATION TRANSMITTAL

(Only for new nonprovisional applications under 37 C.F.R. § 1.53(b))

Attorney Docket No. MI22-1196

First Inventor or Application Identifier Vishnu K. Agarwal et al.

Title See 1 in Addendum

Express Mail Label No. EL373341587 US

APPLICATION ELEMENTS

See MPEP chapter 600 concerning utility patent application contents.

1. ☒ * Fee Transmittal Form (e.g., PTO/SB/17)
(Submit an original and a duplicate for fee processing)
2. ☒ Specification [Total Pages 21] 1
(preferred arrangement set forth below) PLUS TITLE PAGE
 - Descriptive title of the Invention
 - Cross References to Related Applications
 - Statement Regarding Fed sponsored R & D
 - Reference to Microfiche Appendix
 - Background of the Invention
 - Brief Summary of the Invention
 - Brief Description of the Drawings (if filed)
 - Detailed Description
 - Claim(s)
 - Abstract of the Disclosure
3. ☒ Drawing(s) (35 U.S.C. 113) [Total Sheets 3] 1
4. Oath or Declaration [Total Pages 2] 1
 - a. ☒ Newly executed (original or copy)
 - b. ☐ Copy from a prior application (37 C.F.R. § 1.63(d))
(for continuation/divisional with Box 16 completed)
 - i. ☐ DELETION OF INVENTOR(S)
Signed statement attached deleting inventor(s) named in the prior application, see 37 C.F.R. §§ 1.63(d)(2) and 1.33(b).

ADDRESS TO: Assistant Commissioner for Patents
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5. ☐ Microfiche Computer Program (Appendix)
6. Nucleotide and/or Amino Acid Sequence Submission (if applicable, all necessary)
 - a. ☐ Computer Readable Copy
 - b. ☐ Paper Copy (identical to computer copy)
 - c. ☐ Statement verifying identity of above copies

ACCOMPANYING APPLICATION PARTS

7. ☒ Assignment Papers (cover sheet & document(s))
8. ☐ 37 C.F.R. § 3.73(b) Statement of Power of Attorney (when there is an assignee)
9. ☐ English Translation Document (if applicable)
10. ☒ Information Disclosure Statement (IDS)/PTO-1449 ☒ Copies of IDS Citations
11. ☐ Preliminary Amendment
12. ☒ Return Receipt Postcard (MPEP 503)
(Should be specifically itemized)
13. ☐ * Small Entity Statement filed in prior application (PTO/SB/09-12) Status still proper and desired
14. ☐ Certified Copy of Priority Document(s) (if foreign priority is claimed)
15. ☒ Other: Check for \$1154

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Prior application information: Examiner _____ Group / Art Unit: _____

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APPLICATION FOR LETTERS PATENT

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Capacitors Having A Capacitor Dielectric Layer Comprising A Metal Oxide Having Multiple Different Metals Bonded With Oxygen

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ATTORNEY'S DOCKET NO. MI22-1196

1 **Capacitors Having A Capacitor Dielectric Layer Comprising A Metal**
2 **Oxide Having Multiple Different Metals Bonded With Oxygen**

3 **TECHNICAL FIELD**

4 This invention relates to capacitors having a capacitor dielectric
5 layer comprising a metal oxide having multiple different metals bonded
6 with oxygen.

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9 **BACKGROUND OF THE INVENTION**

10 As DRAMs increase in memory cell density, there is a continuing
11 challenge to maintain sufficiently high storage capacitance despite
12 decreasing cell area. Additionally, there is a continuing goal to further
13 decrease cell area. One principal way of increasing cell capacitance is
14 through cell structure techniques. Such techniques include
15 three-dimensional cell capacitors, such as trench or stacked capacitors.
16 Yet as feature size continues to become smaller and smaller,
17 development of improved materials for cell dielectrics as well as the cell
18 structure are important. The feature size of 256Mb DRAMs and
19 beyond will be on the order of 0.25 micron or less, and conventional
20 dielectrics such as SiO_2 and Si_3N_4 might not be suitable because of
21 small dielectric constants.

22 Highly integrated memory devices, such as 256 Mbit DRAMs, are
23 expected to require a very thin dielectric film for the 3-dimensional
24 capacitor of cylindrically stacked or trench structures. To meet this

1 requirement, the capacitor dielectric film thickness will be below 2.5nm
2 of SiO₂ equivalent thickness.

3 Insulating inorganic metal oxide materials (such as ferroelectric
4 materials, perovskite materials and pentoxides) are commonly referred
5 to as "high k" materials due to their high dielectric constants, which
6 make them attractive as dielectric materials in capacitors, for example
7 for high density DRAMs and non-volatile memories. In the context of
8 this document, "high k" means a material having a dielectric constant
9 of at least 11. Such materials include tantalum pentoxide, barium
10 strontium titanate, strontium titanate, barium titanate, lead zirconium
11 titanate and strontium bismuth titanate. Using such materials enables
12 the creation of much smaller and simpler capacitor structures for a
13 given stored charge requirement, enabling the packing density dictated
14 by future circuit design.

15 Certain high k dielectric materials have better current leakage
16 characteristics in capacitors than other high k dielectric materials. In
17 some materials, aspects of a high k material which might be modified
18 or tailored to achieve a highest capacitor dielectric constant possible will
19 unfortunately also tend to hurt the leakage characteristics (i.e., increase
20 current leakage). For example, one class of high k capacitor dielectric
21 materials includes metal oxides having multiple different metals bonded
22 with oxygen, such as the barium strontium titanate, lead zirconium
23 titanate, and strontium bismuth titanate referred to above. For example
24 with respect to barium strontium titanate, it is found that increasing

1 titanium concentration as compared to barium and/or strontium results
2 in improved leakage characteristics, but decreases the dielectric constant.
3 Accordingly, capacitance can be increased by increasing the concentration
4 of barium and/or strontium, but unfortunately at the expense of
5 increasing leakage. Further, absence of titanium in the oxide lattice
6 creates a metal vacancy in such multimetal titanates which can increase
7 the dielectric constant, but unfortunately also increases the current
8 leakage.

9 One method of decreasing leakage while maximizing capacitance
10 is to increase the thickness of the dielectric region in the capacitor.
11 Unfortunately, this is not always desirable. Another prior art method
12 of decreasing leakage is described with respect to Fig. 1. There
13 illustrated is a semiconductor wafer fragment 10 comprising a bulk
14 monocrystalline silicon substrate 12. In the context of this document,
15 the term "semiconductor substrate" or "semiconductive substrate" is
16 defined to mean any construction comprising semiconductive material,
17 including, but not limited to, bulk semiconductive materials such as a
18 semiconductive wafer (either alone or in assemblies comprising other
19 materials thereon), and semiconductive material layers (either alone or
20 in assemblies comprising other materials). The term "substrate" refers
21 to any supporting structure, including, but not limited to, the
22 semiconductive substrates described above. A conductive diffusion
23 region 14 is formed within substrate 12. An insulating dielectric
24 layer 16 is formed over substrate 12, and includes an opening 18

1 formed therein to diffusion region 14. Opening 18 is filled with a
2 suitable conductive material 20, for example conductively doped
3 polysilicon or a metal such as tungsten. Barrier, silicide or other layers
4 might also of course be utilized, but are not otherwise described.

5 A capacitor construction 22 is formed outwardly of insulating
6 dielectric layer 16 and in electrical connection with conductive plugging
7 material 20. Such comprises an inner capacitor electrode 24, an outer
8 capacitor electrode 26, and a capacitor dielectric region 25 sandwiched
9 therebetween. Capacitor dielectric region 25 comprises a composite of
10 three layers 26, 27 and 28. Region 27 comprises a layer of metal
11 oxide having multiple different metals bonded with oxygen, such as
12 barium strontium titanate, fabricated to provide a stoichiometry which
13 maximizes the dielectric constant of the material. As referred to above,
14 this unfortunately adversely affects the desired leakage properties of the
15 layer. Accordingly, layers 26 and 28 are received outwardly of layer 27
16 and comprise a material such as Si_3N_4 which exhibits extremely low
17 current leakage. Unfortunately, Si_3N_4 has a considerably lower dielectric
18 constant than the metal oxides having multiple different metals bonded
19 with oxygen. Such adversely reduces the overall dielectric constant, and
20 accordingly the capacitive effect of capacitor dielectric region 25.

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1 **SUMMARY**

2 The invention comprises capacitors having a capacitor dielectric
3 layer comprising a metal oxide having multiple different metals bonded
4 with oxygen. In one embodiment, a capacitor includes first and second
5 conductive electrodes having a high k capacitor dielectric region
6 positioned therebetween. The high k capacitor dielectric region includes
7 a layer of metal oxide having multiple different metals bonded with
8 oxygen. The layer has varying stoichiometry across its thickness. The
9 layer includes an inner region, a middle region, and an outer region.
10 The middle region has a different stoichiometry than both the inner and
11 outer regions.
12
13

14 **BRIEF DESCRIPTION OF THE DRAWINGS**

15 Preferred embodiments of the invention are described below with
16 reference to the following accompanying drawings.

17 Fig. 1 is a diagrammatic view of a semiconductor wafer fragment
18 processed in accordance with the prior art, as discussed in the
19 "Background" section above.

20 Fig. 2 is a diagrammatic sectional view of a semiconductor wafer
21 fragment in accordance with the invention.

22 Fig. 3 is a diagrammatic view of a chemical vapor deposition
23 chamber utilized in accordance with an aspect of the invention.
24

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

This disclosure of the invention is submitted in furtherance of the constitutional purposes of the U.S. Patent Laws "to promote the progress of science and useful arts" (Article 1, Section 8).

The invention is described in one exemplary structural embodiment as depicted by Fig. 2. Like numerals from the Fig. 1 prior art embodiment are utilized where appropriate, with differences being indicated with different numerals. Fig. 2 depicts a wafer fragment 30 comprising a capacitor 32 having first and second electrodes 24 and 26. Example and preferred materials for electrodes 24 and 26 include conductively doped polysilicon, conductively doped hemispherical grain polysilicon, platinum, ruthenium, ruthenium oxides, iridium, iridium oxides, palladium, tungsten, tungsten nitride, tantalum nitride, titanium nitride, titanium oxygen nitride, and the like.

A high k capacitor dielectric region 35 is positioned between first capacitor electrode 24 and second capacitor electrode 26. Capacitor dielectric region 34 comprises a layer of metal oxide having multiple different metals bonded with oxygen, for example those materials described above. Most preferably and as shown, capacitor dielectric region 35 consists essentially of such layer, meaning no other layers are received intermediate first electrode 24 and second electrode 26 which meaningfully impact the operation or capacitance of capacitor 32. In accordance with but one aspect of the invention, the metal oxide layer having multiple different metals bonded with oxygen has varying

1 stoichiometry across its thickness. In other words, the stoichiometry in
2 such layer is not substantially constant throughout the layer.

3 In accordance with but one aspect of the invention, consider a
4 high k capacitor dielectric region comprising a layer of metal oxide
5 having multiple different metals bonded with oxygen. One of the metals
6 when bonded with oxygen has a first current leakage potential, while
7 another of the metals when bonded with oxygen has a second current
8 leakage potential which is greater than the first current leakage
9 potential. By way of example only, consider a titanate, such as barium
10 strontium titanate. Titanium is an example of one metal which when
11 bonded with oxygen has a lower current leakage potential than either
12 barium or strontium when bonded with oxygen. In this embodiment, the
13 layer comprises at least one portion having a greater concentration of
14 the one metal bonded with oxygen which is more proximate at least
15 one of the first and second electrodes than another portion which is
16 more proximate a center of the layer.

17 By way of example only, capacitor 32 depicts capacitor dielectric
18 region and layer 35 as comprising an inner region 36, a middle
19 region 38, and an outer region 40. Regions 36 and 40 most preferably
20 constitute portions which are fabricated to have a greater concentration
21 of the one metal, in this example titanium, bonded with oxygen than
22 portion 38. Accordingly, regions 40 and 36 are more proximate at least
23 one of the first and second electrodes than is portion 38 more
24 proximate a center of the layer within capacitor dielectric region 35.

Accordingly, the layer or region 35 in this example comprises portions 36 and 40 having a greater concentration of the one metal bonded with oxygen more proximate both the first and second electrodes than the another portion 38 more proximate the center of the layer of capacitor dielectric region 35. Further preferably, region 38 has a greater concentration of the another of the metals (i.e., a greater concentration of one or both of barium and strontium) bonded with oxygen than portions 36 and 40. Further in this preferred example, at least one of portions 36 and 40 (both of such portions as shown) contacts one of the first and second electrodes. As shown, portion 36 contacts electrode 24, while portion 40 contacts electrode 26. Regions 36, 38 and 40 can be fabricated to be the same thickness or different relative thicknesses. Further by way of example only, regions 36 and 40 can be fabricated to comprise essentially the same stoichiometry or different stoichiometries. Accordingly, Fig. 2 depicts but one example where the high k capacitor dielectric region includes a layer where a middle region has a different stoichiometry than both inner and outer regions.

In an additional or alternate aspect or consideration, consider a high k capacitor dielectric region comprising a layer of metal oxide having multiple different metals bonded with oxygen, where one of the metals when bonded with oxygen produces a first material having a first current leakage potential. Further, absence of the one metal in the oxide creates a vacancy and a second material having a second current

leakage potential which is greater than the first current leakage potential. An example would be a multiple metal component titanate, such as barium strontium titanate, where the one metal comprises titanium. In accordance with this implementation, the metal oxide layer comprises at least one portion having a greater concentration of the first material which is more proximate at least one of the first and second electrodes than another portion which is more proximate a center of the layer.

Again, Fig. 2 illustrates an exemplary construction, whereby at least one of portions 36 and 40 can be fabricated to have a greater concentration of the first material than another portion 38. Again using barium strontium titanate as an example, titanium constitutes a metal in such material which, when bonded with oxygen, produces greater current leakage potential or resistance than when a vacancy is created in the oxide by absence of the titanium atoms. Accordingly, barium and strontium quantity could essentially be constant throughout the layer of capacitor dielectric region 35, with only the quantity of titanium varying relative to such regions such as described in the preferred example immediately above.

In an additional or alternate considered aspect of the invention, consider a high k capacitor dielectric region comprising a layer of metal oxide having multiple different metals bonded with oxygen, where one of the metals when bonded with oxygen has a first dielectric constant. Another of the metals of such layer when bonded with oxygen has a

second dielectric constant which is less than the first dielectric constant. The layer comprises at least one portion having a greater concentration of the one metal bonded with oxygen more proximate a center of the layer than another portion more proximate either of the first and second electrodes. By way of example only, barium strontium titanate constitutes one such material. Specifically, barium and strontium in such material constitutes metals which, when bonded with oxygen, produce a first dielectric constant which is greater than when titanium is bonded with oxygen. Accordingly, and again by way of example only and in reference to the above Fig. 2, region 38 constitutes the one portion having a greater concentration of the one metal (i.e., one or both of barium and strontium) bonded with oxygen which is more proximate a center of the layer.

In an additional or alternate considered aspect of the invention, consider a high k capacitor dielectric region comprising a layer of metal oxide having multiple different metals bonded with oxygen, where one of the metals when bonded with oxygen produces a first material having a first dielectric constant. Absence of the one metal in the oxide creates a vacancy, and a second material having a second dielectric constant which is less than the first dielectric constant. The metal oxide layer comprises at least one portion having a greater concentration of the first material which is more proximate a center of the layer than another portion which is more proximate either of the first and second electrodes.

Again using barium strontium titanate as an example, barium and strontium are example metals whose absence in the lattice when producing vacancies results in a dielectric constant which is less than when present. Accordingly in this example with respect to barium strontium titanate, the one metal comprises at least one of barium and strontium. An exemplary construction encompassing the same is again as depicted in Fig. 2.

The above-described preferred embodiment was with respect to multiple component titanates wherein both the current leakage potential and dielectric constant aspects of the invention are met in the same material. Alternate materials are also, of course, contemplated whereby perhaps only one of the current leakage potential relationship or the capacitor dielectric constant relationship results, with the invention only being limited by the accompanying claims appropriately interpreted in accordance with the Doctrine of Equivalents.

Fig. 3 depicts an exemplary process of depositing a dielectric layer comprising metal oxide having multiple different metals bonded with oxygen in accordance with an aspect of the invention. A chemical vapor deposition chamber 70 has a substrate 72 upon which deposition is desired positioned therein. Exemplary multiple gas inlets 76, 77, 78 and 80 are depicted schematically as extending to chamber 70. Fewer or more gas inlets could, of course, be provided. Further, gases could be mixed further upstream of the schematic depicted by Fig. 3, and flowed as mixtures or combinations relative to one or more inlets.

Multiple gaseous precursors are fed to the chamber under conditions effective to deposit the dielectric layer having multiple different metals bonded with oxygen on substrate 72. At least some of the precursors comprise different metals of the respective multiple different metals bonded with oxygen, which is deposited in the layer on the substrate. As one example, a process for depositing (Ba,Sr) TiO₃ includes utilizing precursors of Ba(DPM)₂, Sr(DPM)₂ and Ti(OC₃H₇)₄, O₂ at 0.5 Torr and 410°C, where "DPM" denotes "dipivaloylmethanato". For example, one of each of these gases could be flowed from the respective inlets 76, 77, 78 and 80. In accordance with one implementation, the flow of at least one of the precursors is varied during the feeding to achieve different concentrations of the different metals bonded with oxygen at different depths in the deposited layer.

In compliance with the statute, the invention has been described in language more or less specific as to structural and methodical features. It is to be understood, however, that the invention is not limited to the specific features shown and described, since the means herein disclosed comprise preferred forms of putting the invention into effect. The invention is, therefore, claimed in any of its forms or modifications within the proper scope of the appended claims appropriately interpreted in accordance with the doctrine of equivalents.

CLAIMS:

1. A capacitor comprising first and second conductive electrodes having a high k capacitor dielectric region positioned therebetween, the high k capacitor dielectric region comprising a layer of metal oxide having multiple different metals bonded with oxygen, the layer having varying stoichiometry across its thickness, the layer comprising an inner region, a middle region, and an outer region, the middle region having a different stoichiometry than both the inner and outer regions.

2. The capacitor of claim 1 wherein the inner and outer regions have essentially the same stoichiometry.

3. The capacitor of claim 1 wherein the metal oxide with multiple different metals bonded with oxygen comprises a ferroelectric material.

4. The capacitor of claim 1 the capacitor dielectric region consists essentially of the layer.

1 5. A capacitor comprising first and second conductive electrodes
2 having a high k capacitor dielectric region positioned therebetween, the
3 high k capacitor dielectric region comprising a layer of metal oxide
4 having multiple different metals bonded with oxygen, one of the metals
5 when bonded with oxygen having a first current leakage potential,
6 another of the metals when bonded with oxygen having a second current
7 leakage potential which is greater than the first current leakage
8 potential, the layer comprising at least one portion having a greater
9 concentration of the one metal bonded with oxygen which is more
10 proximate at least one of the first and second electrodes than another
11 portion more proximate a center of the layer.

12
13 6. The capacitor of claim 5 wherein the another portion has
14 a greater concentration of the another of the metals bonded with
15 oxygen than the one portion.

16
17 7. The capacitor of claim 5 wherein the layer comprises
18 portions having a greater concentration of the one metal bonded with
19 oxygen more proximate both the first and second electrodes than the
20 another portion more proximate the center of the layer.

21
22 8. The capacitor of claim 5 wherein the at least one portion
23 contacts the one electrode.
24

1 9. The capacitor of claim 5 wherein the layer comprises
2 portions having a greater concentration of the one metal bonded with
3 oxygen more proximate both the first and second electrodes than the
4 another portion more proximate the center of the layer, said greater
5 concentration portions respectively contacting the first and second
6 electrodes.

7
8 10. The capacitor of claim 5 wherein the metal oxide with
9 multiple different metals bonded with oxygen comprises a titanate, and
10 the one metal comprises titanium.

11
12 11. The capacitor of claim 5 the capacitor dielectric region
13 consists essentially of the layer.

12. A capacitor comprising first and second conductive electrodes having a high k capacitor dielectric region positioned therebetween, the high k capacitor dielectric region comprising a layer of metal oxide having multiple different metals bonded with oxygen, one of the metals when bonded with oxygen producing a first material having a first current leakage potential, absence of the one metal in the oxide creating a vacancy and a second material having a second current leakage potential which is greater than the first current leakage potential, the layer comprising at least one portion having a greater concentration of the first material which is more proximate at least one of the first and second electrodes than another portion more proximate a center of the layer.

13. The capacitor of claim 12 wherein the layer comprises portions having a greater concentration of the first material more proximate both the first and second electrodes than the another portion more proximate a center of the layer.

14. The capacitor of claim 12 wherein the at least one portion contacts the one electrode.

1 15. The capacitor of claim 12 wherein the layer comprises
2 portions having a greater concentration of the first material more
3 proximate both the first and second electrodes than the another portion
4 more proximate a center of the layer, said greater concentration
5 portions respectively contacting the first and second electrodes.
6

7 16. The capacitor of claim 12 wherein the metal oxide with
8 multiple different metals bonded with oxygen comprises a titanate, and
9 the one metal comprises titanium.
10

11 17. The capacitor of claim 12 the capacitor dielectric region
12 consists essentially of the layer.
13

14 18. A capacitor comprising first and second conductive electrodes
15 having a high k capacitor dielectric region positioned therebetween, the
16 high k capacitor dielectric region comprising a layer of metal oxide
17 having multiple different metals bonded with oxygen, one of the metals
18 when bonded with oxygen having a first dielectric constant, another of
19 the metals when bonded with oxygen having a second dielectric constant
20 which is less than the first dielectric constant, the layer comprising at
21 least one portion having a greater concentration of the one metal
22 bonded with oxygen more proximate a center of the layer than another
23 portion more proximate either of the first and second electrodes.
24

1 19. The capacitor of claim 18 wherein the another portion
2 contacts one of the first and second electrodes.

3
4 20. The capacitor of claim 18 wherein the another portion has
5 a greater concentration of the another of the metals bonded with
6 oxygen than the one portion.

7
8 21. The capacitor of claim 18 wherein the layer comprises
9 portions having a greater concentration of the another metal bonded
10 with oxygen more proximate both the first and second electrodes than
11 the one portion more proximate the center of the layer, said greater
12 concentration portions respectively contacting the first and second
13 electrodes.

14
15 22. The capacitor of claim 18 the capacitor dielectric region
16 consists essentially of the layer.

17
18 23. The capacitor of claim 18 wherein the metal oxide with
19 multiple different metals bonded with oxygen comprises a titanate, and
20 the another metal comprises titanium.

1 24. The capacitor of claim 18 wherein the metal oxide with
2 multiple different metals bonded with oxygen comprises barium strontium
3 titanate, and the one metal comprises at least one of barium and
4 strontium.

5
6 25. A capacitor comprising first and second conductive electrodes
7 having a high k capacitor dielectric region positioned therebetween, the
8 high k capacitor dielectric region comprising a layer of metal oxide
9 having multiple different metals bonded with oxygen, one of the metals
10 when bonded with oxygen producing a first material having a first
11 dielectric constant, absence of the one metal in the oxide creating a
12 vacancy and a second material having a second dielectric constant which
13 is less than the first dielectric constant, the layer comprising at least
14 one portion having a greater concentration of the first material which
15 is more proximate a center of the layer than another portion more
16 proximate either of the first and second electrodes.

17
18 26. The capacitor of claim 25 wherein the layer comprises
19 portions having a greater concentration of the first material more
20 proximate both the first and second electrodes than the another portion
21 more proximate a center of the layer.

22
23 27. The capacitor of claim 25 wherein the another portion
24 contacts the one electrode.

1 28. The capacitor of claim 25 wherein the layer comprises
2 portions having a greater concentration of the another material more
3 proximate both the first and second electrodes than the one portion
4 more proximate a center of the layer, said greater concentration
5 portions respectively contacting the first and second electrodes.
6

7 29. The capacitor of claim 25 the capacitor dielectric region
8 consists essentially of the layer.
9

10 30. The capacitor of claim 25 wherein the metal oxide with
11 multiple different metals bonded with oxygen comprises a titanate.
12

13 31. The capacitor of claim 25 wherein the metal oxide with
14 multiple different metals bonded with oxygen comprises barium strontium
15 titanate, and the one metal comprises at least one of barium and
16 strontium.
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1 **ABSTRACT OF THE DISCLOSURE**

2 The invention comprises capacitors having a capacitor dielectric
3 layer comprising a metal oxide having multiple different metals bonded
4 with oxygen. In one embodiment, a capacitor includes first and second
5 conductive electrodes having a high k capacitor dielectric region
6 positioned therebetween. The high k capacitor dielectric region includes
7 a layer of metal oxide having multiple different metals bonded with
8 oxygen. The layer has varying stoichiometry across its thickness. The
9 layer includes an inner region, a middle region, and an outer region.
10 The middle region has a different stoichiometry than both the inner and
11 outer regions.

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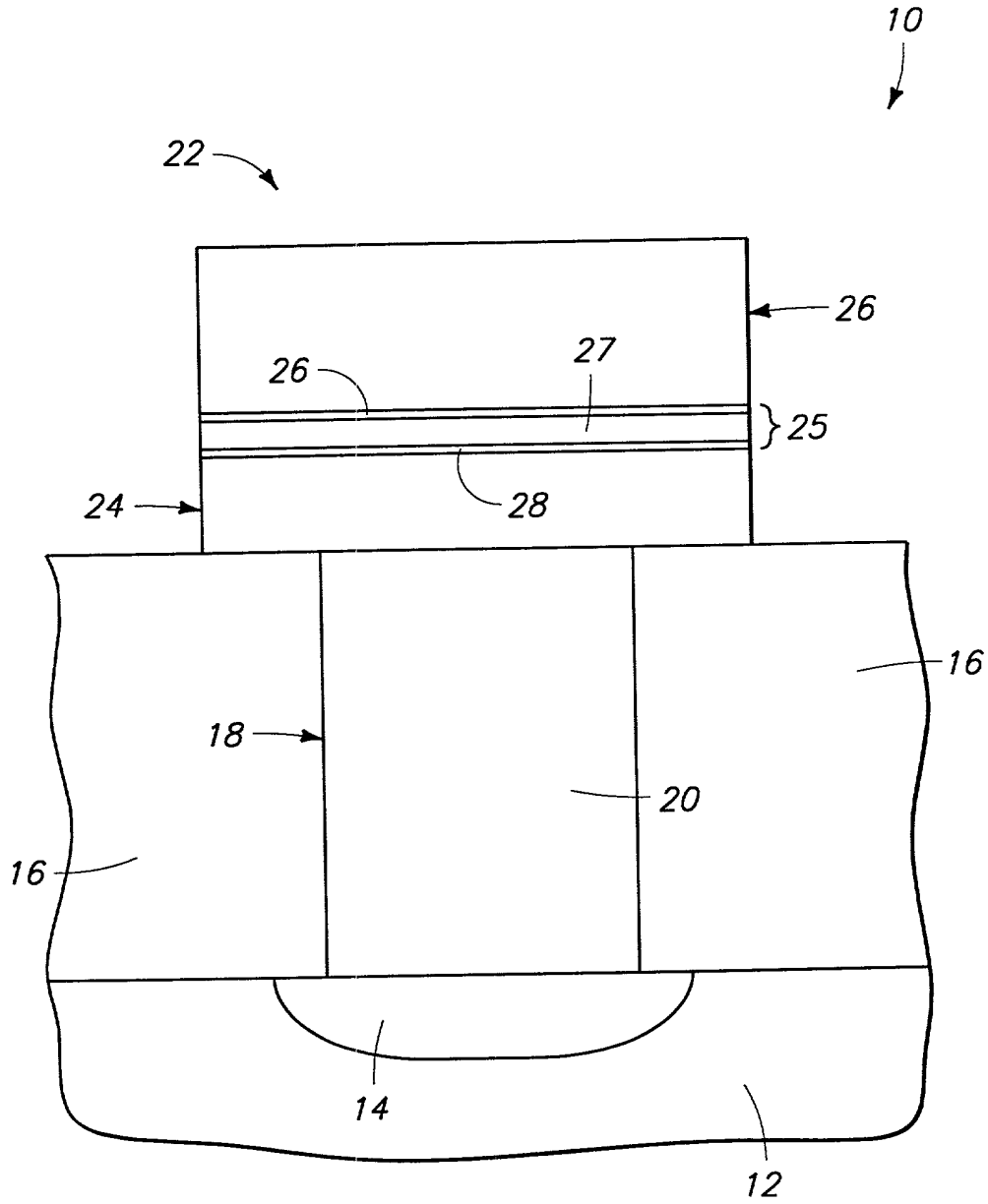
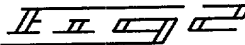
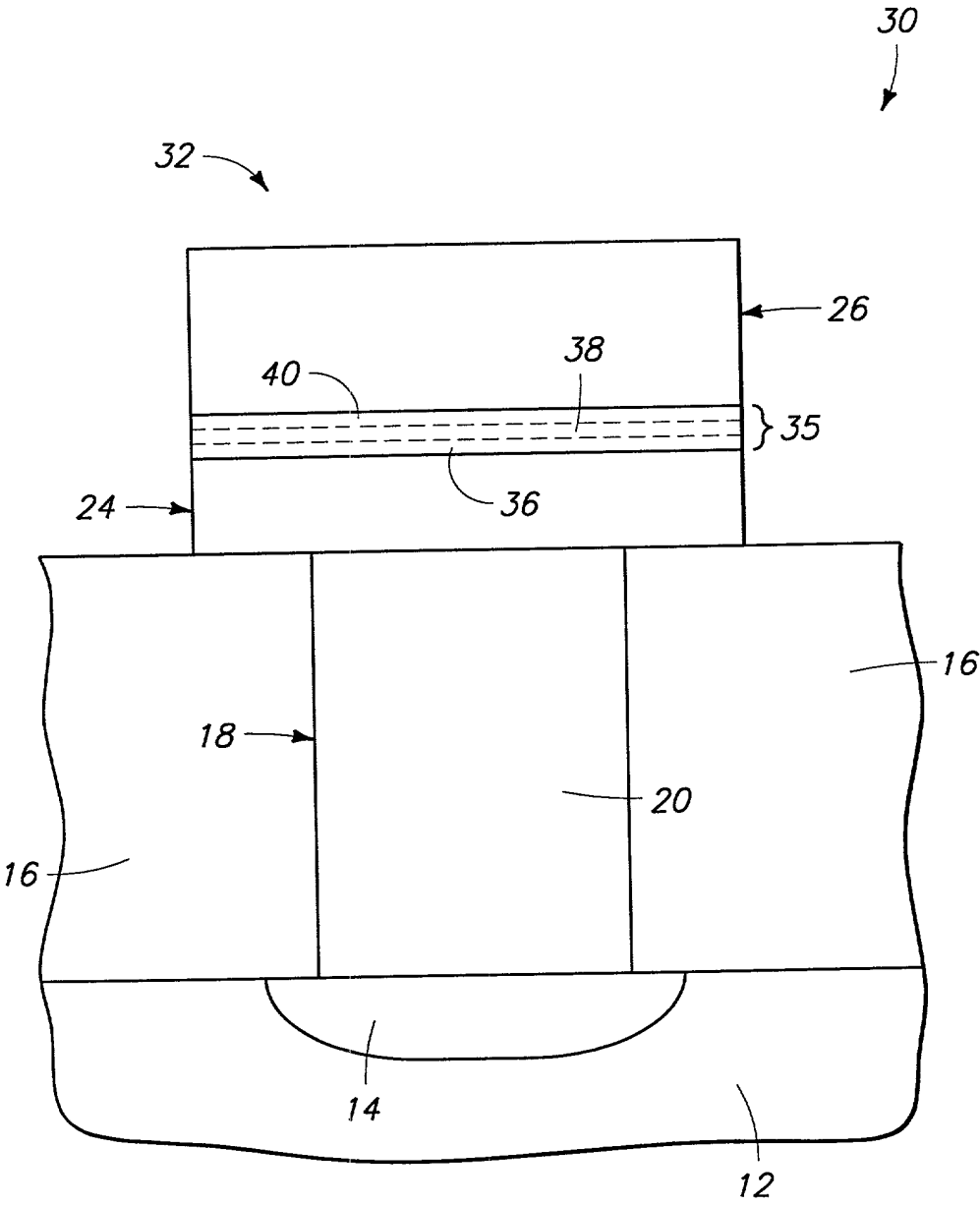
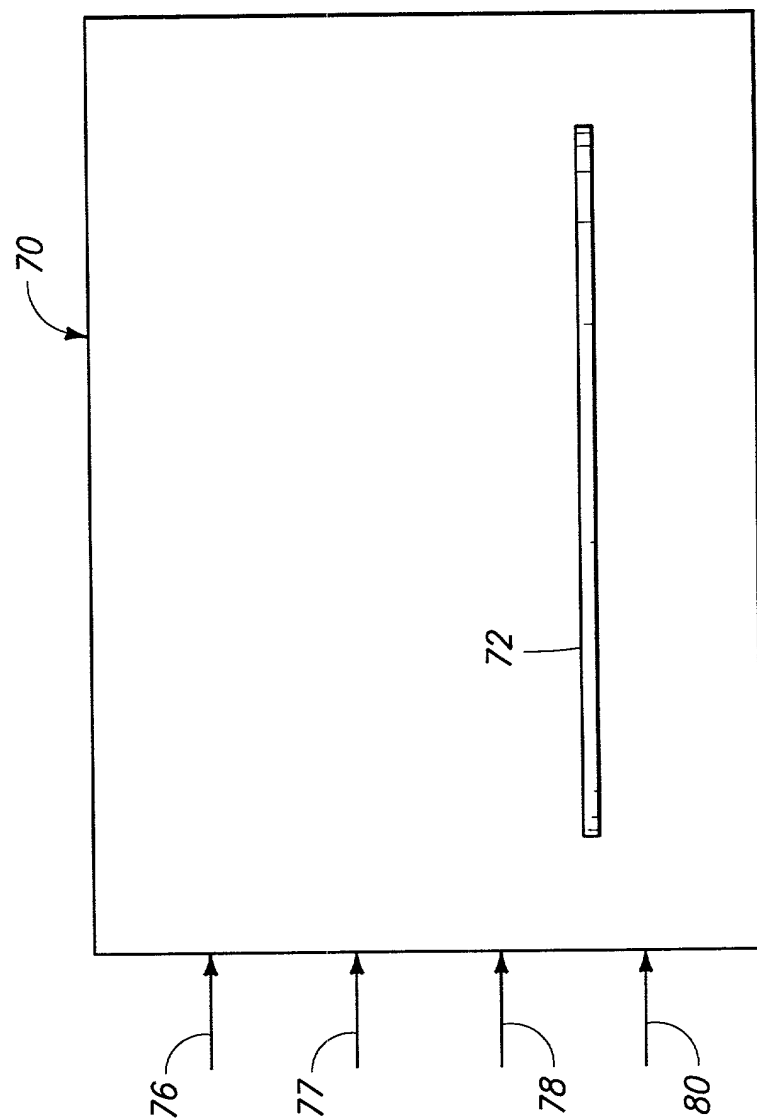


FIG. 1
PRIOR ART





EE

DECLARATION OF JOINT INVENTORS FOR PATENT APPLICATION

As the below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and joint inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled: Capacitors Having a Capacitor Dielectric Layer Comprising a Metal Oxide Having Multiple Different Metals Bonded With Oxygen, the specification of which is attached hereto.

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims.

I acknowledge the duty to disclose information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations §1.56.

PRIOR FOREIGN APPLICATIONS:

I hereby state that no applications for foreign patents or inventor's certificates have been filed prior to the date of execution of this declaration.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful

false statement may jeopardize the validity of the application or any patent issued therefrom.

* * * * *

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